

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



April 2013

FDP7N50

N-Channel UniFETTM MOSFET

500 V, 7 A, 900 mΩ

Features

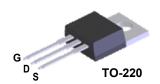
- $R_{DS(on)} = 900 \text{ m}\Omega \text{ (Max.)} @ V_{GS} = 10 \text{ V, } I_D = 3.5 \text{ A}$
- Low Gate Charge (Typ. 12.8 nC)
- Low C_{rss} (Typ. 9 pF)
- · 100% Avalanche Tested

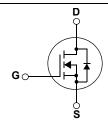
Applications

- ALCD/LED TV
- Lighting
- · Uninterruptible Power Supply
- · AC-DC Power Supplypplications

Description

UniFETTM MOSFET is Fairchild Semiconductor[®]'s high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings

Symbol	Parameter		FDP7N50	Unit		
V _{DSS}	Drain-Source Voltage		500	V		
I _D	Drain Current	- Continuous (T _C = 25°C) - Continuous (T _C = 100°C)		7 4.2	A A	
I _{DM}	Drain Current	- Pulsed	(Note 1)	28	A	
V _{GSS}	Gate-Source voltage		±30	V		
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	270	mJ	
I _{AR}	Avalanche Current		(Note 1)	7	A	
E _{AR}	Repetitive Avalanche Energy		(Note 1)	8.9	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		(Note 3)	4.5	V/ns	
P _D	Power Dissipation	(T _C = 25°C) - Derate above 25°C		89 0.71	W W/°C	
T _{J,} T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C		
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C		

Thermal Characteristics

Symbol	Parameter	FDP7N50	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max. 1.4			
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.5	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5		

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP7N50	FDP7N50	TO-220		-	50

$\textbf{Electrical Characteristics} \quad \textbf{T}_{\text{C}} = 25^{\circ}\text{C unless otherwise noted}$

Symbol	Parameter	Conditions	Min.	Тур.	Max	Unit
Off Charac	teristics			ı		ı
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	500			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C		0.5		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500V, V _{GS} = 0V V _{DS} = 400V, T _C = 125°C			1 10	μ Α μ Α
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 3.5A		0.76	0.9	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40V, I _D = 3.5A		2.5		S
Dynamic C	haracteristics	•		•		
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V,		720	940	pF
C _{oss}	Output Capacitance	f = 1.0MHz		95	190	pF
C _{rss}	Reverse Transfer Capacitance			9	13.5	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 250V, I_{D} = 7A$	ı	6	20	ns
t _r	Turn-On Rise Time	$R_G = 25\Omega$	ı	55	120	ns
$t_{d(off)}$	Turn-Off Delay Time		ı	25	60	ns
t _f	Turn-Off Fall Time	(Note 4)		35	80	ns
Q_g	Total Gate Charge	V _{DS} = 400V, I _D = 7A	-	12.8	16.6	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 10V	-	3.7		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		5.8		nC
Drain-Sour	rce Diode Characteristics and Maximun	n Ratings		·		
I _S	Maximum Continuous Drain-Source Diode Forward Current				7	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				28	Α
V_{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 7A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 7A		275		ns
Q _{rr}	Reverse Recovery Charge	dl _F /dt =100A/μs		1.7		μС

NOTES

 $^{{\}bf 1.}\ {\bf Repetitive}\ {\bf Rating:}\ {\bf Pulse}\ {\bf width}\ {\bf limited}\ {\bf by}\ {\bf maximum}\ {\bf junction}\ {\bf temperature}$

^{2.} I $_{AS}$ = 7A, V $_{DD}$ = 50V, L=10mH, R $_{G}$ = 25 Ω , Starting T $_{J}$ = 25 $^{\circ}$ C

^{3.} $I_{SD} \le 7 A$, di/dt $\le 200 A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting T_J = 25°C

^{4.} Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

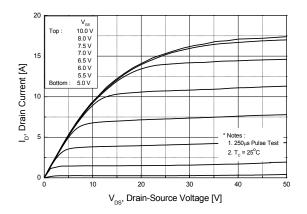


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

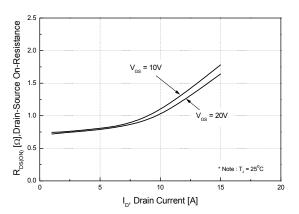


Figure 5. Capacitance Characteristics

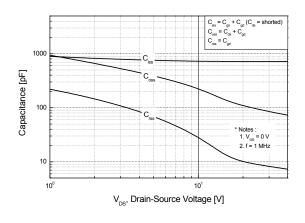


Figure 2. Transfer Characteristics

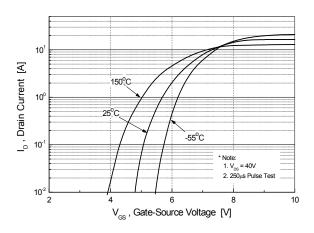


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

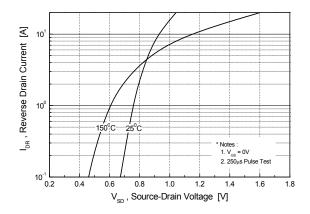
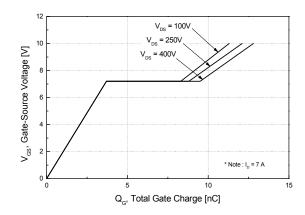


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

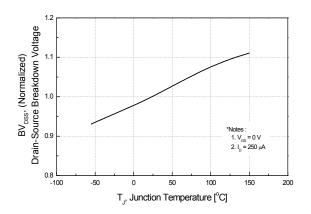


Figure 8. On-Resistance Variation vs. Temperature

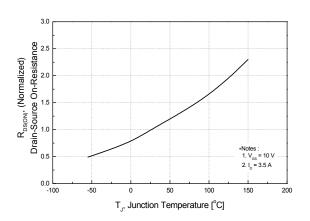


Figure 9. Maximum Safe Operating Area - FDP7N50

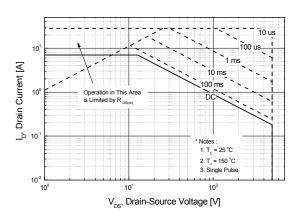


Figure 10. Maximum Drain Current vs. Case Temperature

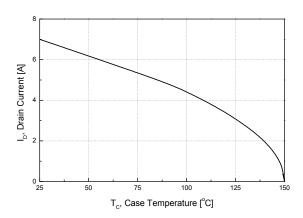
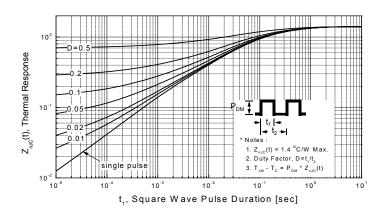
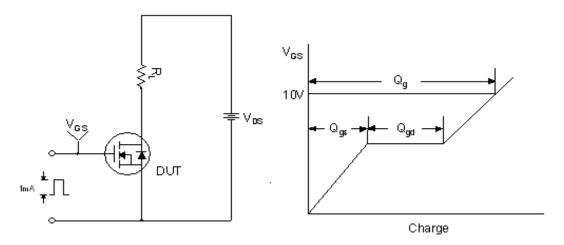


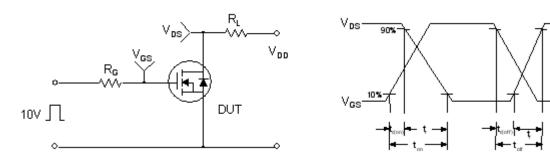
Figure 11. Transient Thermal Response Curve



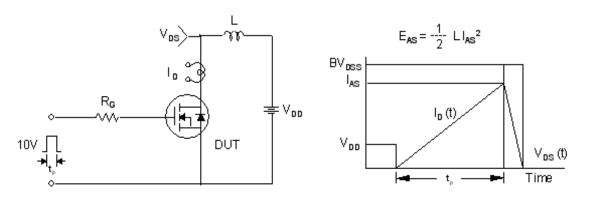
Gate Charge Test Circuit & Waveform



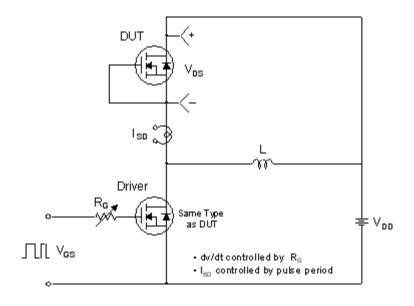
Resistive Switching Test Circuit & Waveforms

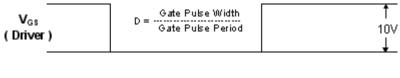


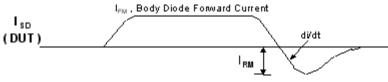
Unclamped Inductive Switching Test Circuit & Waveforms

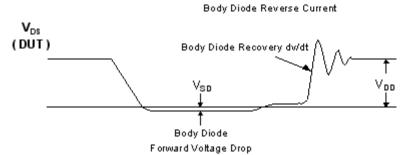


Peak Diode Recovery dv/dt Test Circuit & Waveforms



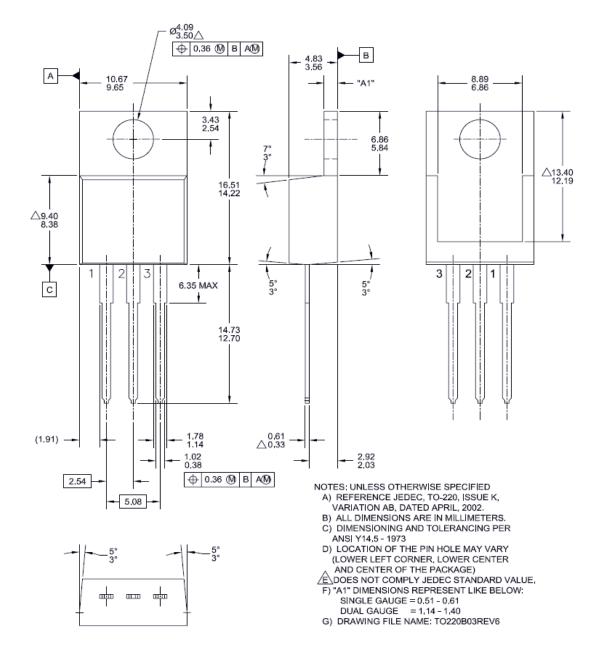






Mechanical Dimensions

TO-220B03







TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

2Cool™ FPS™ F-PFS™ AccuPower™ FRFET® AX-CAP® BitSiC™ Global Power ResourceSM Green Bridge™ Build it Now™ CorePLUS™ Green FPS™ CorePOWER™ Green FPS™ e-Series™ CROSSVOLTTM Gmax™ GTO™

IntelliMAX™ Current Transfer Logic™ ISOPLANAR™ DEUXPEED® Dual Cool™ Marking Small Speakers Sound Louder and Better™

EcoSPARK® MegaBuck™ EfficentMax™ MIČROCOUPLER™ ESBC™ MicroFET™

MicroPak™ MicroPak2™ Fairchild® MillerDrive™ Fairchild Semiconductor® MotionMax™ FACT Quiet Series™ mWSaver™ FACT[®] OptoHiT™ FAST[®] OPTOLOGIC® FastvCore™ OPTOPLANAR® FETBench™

PowerTrench® PowerXS™

Programmable Active Droop™

QFET QSTM Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™ SignalWise™

SmartMax™ SMART START™

Solutions for Your Success™

SPM®

STEALTH™ SuperFET® SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS® SvncFET™

Sync-Lock™

SYSTEM ®*

GENERAL

TipyBoost™ TinyBoost Tinẏ́Buck™ TinyCalc™ TinyLogic[®] TINYOPTO™ TinvPower™ TinyPWM™ TinyWire™ TranSiC® TriFault Detect™

TRUECURRENT®* μSerDes™

UHC[®] Ultra FRFET™ UniFET™ VCX™ VisualMax™ VoltagePlus™ XSTM

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMERFAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY
FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS **Definition of Terms**

Datasheet Identification Product Status		Definition		
Advance Information Formative / In Design		Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.		
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.		

Rev. 164

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hol

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative